



## Silicon Carbide Schottky Diode

$V_{RRM}$	650 V
$I_F$ 127°C	6 A
$Q_C$	25 nC

### Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical



	SYMBOL	UNIT	VALUE
Reverse Voltage Surge Peak 4 Tc 125 °C	$V_{RSM}$	V	650
Reverse Voltage DC 4 Tc 125 °C	$V_{DC}$	V	650
Continuous Forward Current 4 Tc 25 °C	$I_F$	A	12
Continuous Forward Current 4 Tc 175 °C			6
Non-repetitive peak forward surge current 4 Tc 125 °C tp 10ms <al Z Sine Ka je	$I_{FSM}$	A	65
Power Dissipation 4 Tc 25 °C	$P_{TOT}$	K	1
Power Dissipation 4 Tc 110 °C			1
IFT Value 4 Tc 125 °C tp 10ms	$i^2dt$	A	



# YJD106506FQG2

## Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	$V_F$	V	$I_F=6A, T_J=25^{\circ}C$	1.31	1.5
			$I_F=6A, T_J=175^{\circ}C$	1.65	-
Reverse leakage current	$I_R$	$\mu A$	$V_R=650V, T_J=25^{\circ}C$	0.5	25
			$V_R=650V, T_J=175^{\circ}C$	5	-
Total capacitive charge	$Q_C$	nC	$V_R=400V, T_J=25^{\circ}C, Q_C=\int_0^{V_R} C(V)dV$	25	-
Total capacitance	C	$\mu F$	$V_R=0V, f=1MHz$	378	-
			$V_R=200V, f=1MHz$	51	-
			$V_R=400V, f=1MHz$	49	-
Capacitance Stored Energy	$E_C$	$\mu J$	$V_R=400V$	3	-

## Thermal Characteristics ( $T_a=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{J-C}$	$^{\circ}C/W$	4.76

## Typical Characteristics

Figure 1. Forward CharacterCharacteristi

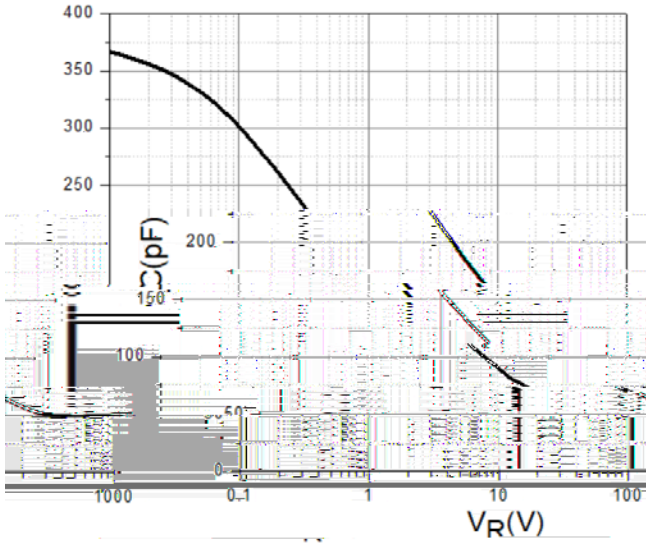


Figure 3. Capacitance vs. Reverse Voltage

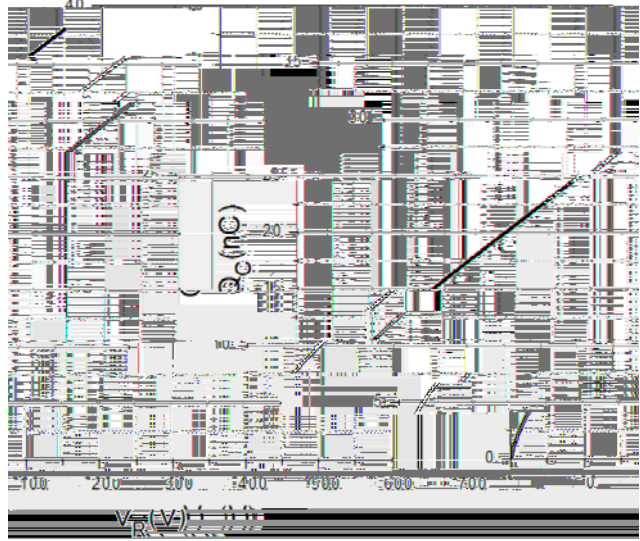


Figure 4. Total Capacitance Charge vs. Reverse Voltage

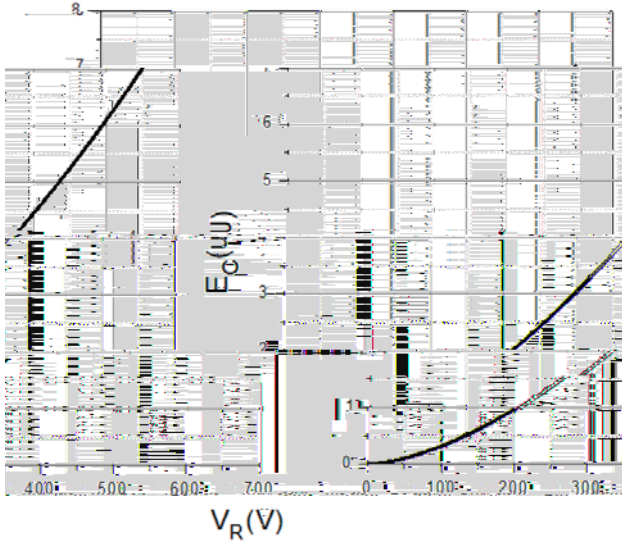


Figure 5. Capacitance Stored Energy

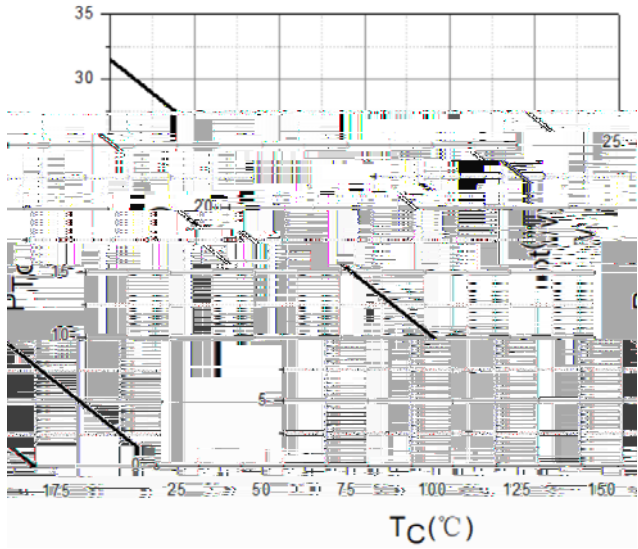


Figure 6. Power Derating

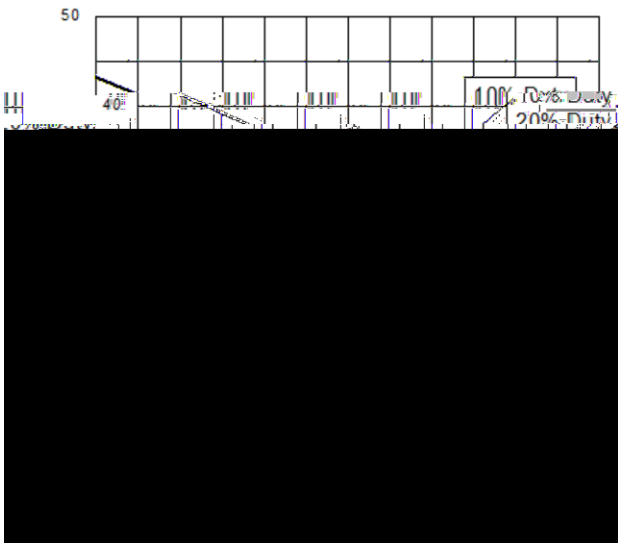


Figure 7. Current Derating

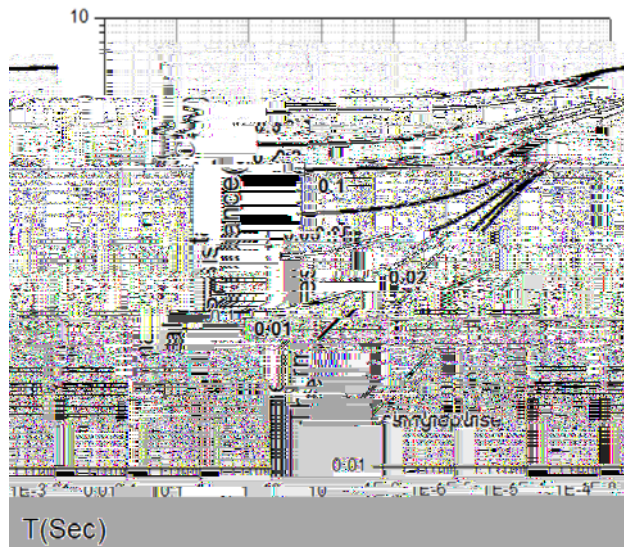
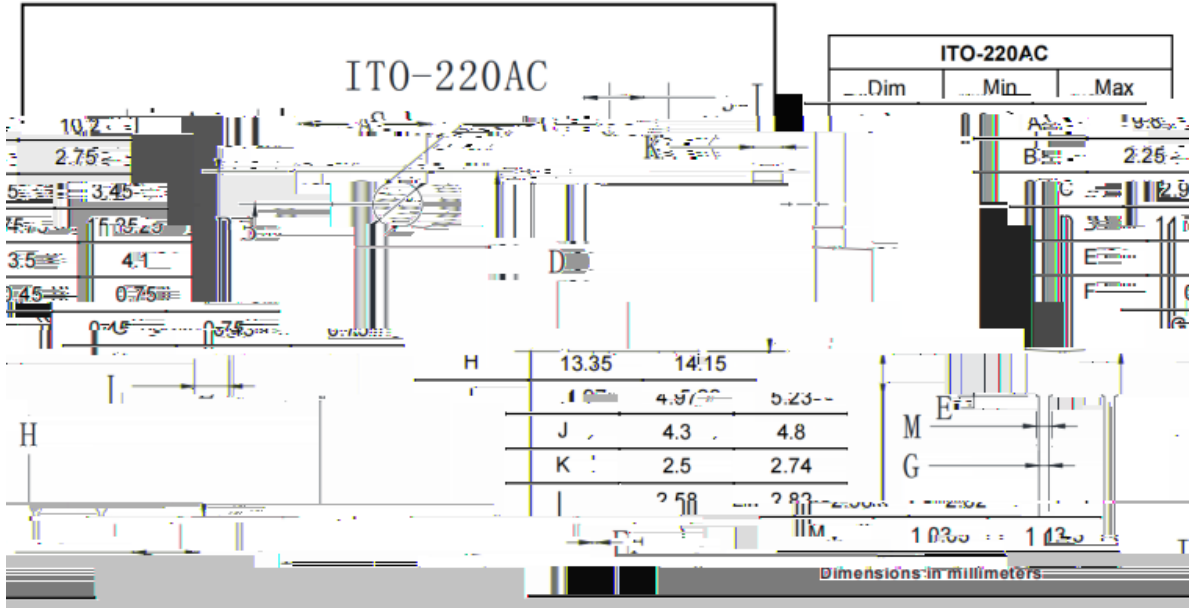


Figure 8. Transient Thermal Impedance



# YJD106506FQG2

## Outline Dimensions



'LVFODLPHU

7KH LQIRUPDQWRIC \$ QHWKLV GRFXPHQW<DQJ RKR X HIBQJHQZHHF(ROHFOVRUR Q&RF /VHG UHV  
ULJKW WR PDNH FKD QJHRU ZW WIK R/XSM RHR SLDRC XRF Q' R IGWV SFCDA RYGHKUHUCILDEWQGMV L JXQ F  
RU RWKHUZLVH

7KH SURGXFW OLVWJCH G HWRI LEH LXW B G VZH FWKURRQG IEQHTUX L S PHQW RU GHYLFHWWKDQG Q  
HTXLSPHQW RU GHYLLFHH K IZJKL FKH VHHOGRW K H PLDDEIXOLFWML B QX RIG QGLEDJHFHUOK XPFKQDQVLIH  
PHGLFDO LQVWUXPHRQV HT XLSRQWSSRUFHMDUFAK LQX FOH DU UHDFVKRHO FFROQWUURROOHUW D Q  
GHYLFHV <DQJMLHW R LE HDIDR Q HDR/Q XLP H O LQRI R HV S IRDE/LCEL W/H V R O VDIQQ JGIDJRPJMMFK LP  
RI VDOH

7KLV SXEOLFDWLR G SVCSFHUW HDGIVLQ URQAPDXLSRQL H G H YRUR XDGGLRQL FSOCHD V B WRHJPLW R X  
KWVZZ \DQJMLH FRP